







OPA132, OPA2132, OPA4132

SBOS054C - JANUARY 1995 - REVISED AUGUST 2024

OPAx132 High-Speed FET-Input Operational Amplifiers

1 Features

A newer version of this device is now available: **OPA2156**

FET input: $I_B = 50pA$ Maximum

Wide bandwidth: 8MHz High slew rate: 20V/µs Low noise: 8nV/√Hz (1kHz) Low distortion: 0.00008%

High open-loop gain: 126dB ($2k\Omega$ load) Wide supply range: ±2.5V to ±18V Low offset voltage: 500µV maximum Single, dual, and quad versions

2 Applications

SAR ADC driver

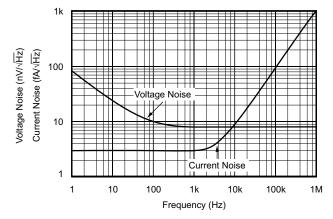
Voltage reference buffer

Trans-impedance amplifier

Photodiode amplifier

Active filter

Integrator



Low-Noise JFET Input

3 Description

The OPA132, OPA2132, and OPA4132 (OPAx132) series of FET-input operational amplifiers provides high speed and excellent dc performance. The combination of high slew rate and wide bandwidth provide fast settling time. The single, and quad versions have identical specifications for maximum design flexibility. High-performance grades are available in the single and dual versions. All are an excellent choice for generalpurpose, audio, data-acquisition, and communications applications, especially where high source impedance is encountered.

The OPAx132 operational amplifiers are easy to use and free from phase inversion and overload problems often found in common FET-input operational amplifiers. Input cascode circuitry provides excellent common-mode rejection and maintains low input bias current over the wide input voltage range. The OPAx132 series of operational amplifiers are stable in unity gain and provide excellent dynamic behavior over a wide range of load conditions, including high load capacitance. Dual and quad versions feature completely independent circuitry for lowest crosstalk and freedom from interaction, even when overdriven or overloaded.

The single version is available in 8-pin SOIC surface mount package, the dual version is available in 8-pin DIP and SOIC surface-mount packages. The quad version is available in SOIC surface-mount packages. All are specified for -40°C to +85°C operation.

The OPA2156 is a next-generation version, offering lower broadband noise (3nV/\(\sqrt{Hz}\)), wider bandwidth (25MHz), and rail-to-rail inputs.

Device Information

PART NUMBER	CHANNEL COUNT	PACKAGE ⁽¹⁾
OPA132	Single D (SOIC, 8)	
OPA2132	Dual	D (SOIC, 8)
	Duai	P (PDIP,8)
OPA4132	A4132 Quad D (SOIC, 14)	

For more information, see Section 10.



Table of Contents

1 Features1	6.4 Device Functional Modes	11
2 Applications1	7 Application and Implementation	12
3 Description1	7.1 Application Information	12
4 Pin Configuration and Functions3	7.2 Typical Application	
5 Specifications5	7.3 Power Supply Recommendations	14
5.1 Absolute Maximum Ratings5	7.4 Layout	14
5.2 ESD Ratings5	8 Device and Documentation Support	16
5.3 Recommended Operating Conditions5	8.1 Device Support	16
5.4 Thermal Information - OPA1326	8.2 Documentation Support	
5.5 Thermal Information - OPA21326	8.3 Receiving Notification of Documentation Updates	16
5.6 Thermal Information - OPA41326	8.4 Support Resources	16
5.7 Electrical Characteristics7	8.5 Trademarks	16
5.8 Typical Characteristics8	8.6 Electrostatic Discharge Caution	17
6 Detailed Description11	8.7 Glossary	17
6.1 Overview	9 Revision History	17
6.2 Functional Block Diagram11	10 Mechanical, Packaging, and Orderable	
6.3 Feature Description11	Information	18



4 Pin Configuration and Functions

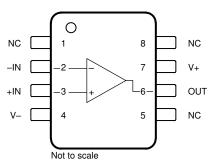


Figure 4-1. OPA132: D Package, 8-Pin SOIC (Top View)

Pin Functions: OPA132

	PIN	TYPE	DESCRIPTION		
NAME	NO.	ITPE	DESCRIPTION		
+IN	3	Input	Noninverting input		
-IN	2	Input	Inverting input		
NC	1, 5	_	Do not connect these pins ⁽¹⁾		
NC	8	_	No internal connection. Float this pin.		
Output	6	Output	Output		
V+	7	Power	Positive power supply		
V-	4	Power	Negative power supply		

(1) Existing layouts for the OPA132 before revision C of this data sheet do not need to be redesigned.

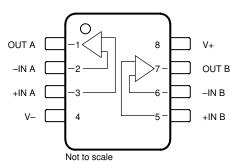


Figure 4-2. OPA2132: D Package, 8-Pin SOIC, and P Package, 8-Pin PDIP (Top View)

Table 4-1. Pin Functions: OPA2132

P	IN	TYPE	DESCRIPTION	
NAME	NO.	ITPE	DESCRIPTION	
+IN A	3	Input	Noninverting input, channel A	
+IN B	5	Input	Noninverting input, channel B	
–IN A	2	Input	ng input, channel A	
–IN B	6	Input	ting input, channel B	
OUT A	1	Output	Output, channel A	
OUT B	7	Output	Output, channel B	
V+	8	Power	Positive (highest) power supply	
V-	4	Power	Negative (lowest) power supply	



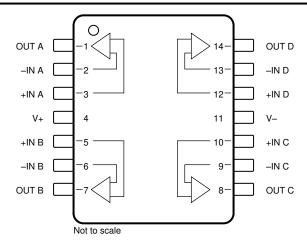


Figure 4-3. OPA4132- D Package, 14-Pin SOIC (Top View)

Table 4-2. Pin Functions: OPA4132

	PIN	TVDE	DECORPORTOR			
NAME	NO.	TYPE	DESCRIPTION			
+IN A	3	Input	Noninverting input, channel A			
+IN B	5	Input	Noninverting input, channel B			
+IN C	10	Input	Noninverting input, channel C			
+IN D	12	Input	erting input, channel D			
–IN A	2	Input	Inverting input, channel A			
–IN B	6	Input	Inverting input, channel B			
–IN C	9	Input	Inverting input, channel C			
–IN D	13	Input	Inverting input, channel D			
OUT A	1	Output	Output, channel A			
OUT B	7	Output	Output, channel B			
OUT C	8	Output	Output, channel C			
OUT D	14	Output	Output, channel D			
V+	4	Power	Positive (highest) power supply			
V–	11	Power	Negative (lowest) power supply			

Submit Document Feedback

Copyright © 2024 Texas Instruments Incorporated



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Vs	Supply voltage, (V+) – (V–)		36	V
	Input voltage ⁽²⁾	(V-) - 0.5	(V+) + 0.5	V
	Input current ⁽²⁾		±10	mA
I _{SC}	Output short-circuit ⁽³⁾	Contin	uous	
T _A	Operating temperature	-40	125	°C
TJ	Junction temperature		150	°C
T _{stg}	Storage temperature	-55	125	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails must be current limited to 10mA or less.
- (3) Short-circuit to ground, one amplifier per package.

5.2 ESD Ratings

			VALUE	UNIT	
OPA132	in SOIC Package, OPA2132	in PDIP Package			
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V	
OPA213	2 in SOIC Package				
V		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾		V	
V _(ESD) Electrostatic discharge		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	V	
OPA413	2				
V	Floatroatatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000		
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±200	V	

⁽¹⁾ JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _S Supply voltage, (V+) – (V–)	Supply voltage (V+) (V)	Dual supply	±2.5	±15	±18	V
	Supply voltage, (v+) = (v=)	Single supply	9	30	36	
T _A	Ambient temperature		-40		85	°C

⁽²⁾ JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.



5.4 Thermal Information - OPA132

		OPA132	
	THERMAL METRIC ⁽¹⁾	D (SOIC)	UNIT
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	160	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	75	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	60	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	9	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	50	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.5 Thermal Information - OPA2132

		OPA	A2132	
	THERMAL METRIC ⁽¹⁾	D (SOIC)	P (PDIP)	UNIT
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	160	71	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	75	50	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	60	36	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	9	16	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	50	35	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.6 Thermal Information - OPA4132

		OPA4132		
	THERMAL METRIC ⁽¹⁾	D (SOIC)	UNIT	
		14 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	97	°C/W	
R _{θJC(top)}	Junction-to-case (top) thermal resistance	56	°C/W	
R _{θJB}	Junction-to-board thermal resistance	53	°C/W	
Ψ_{JT}	Junction-to-top characterization parameter	19	°C/W	
Ψ_{JB}	Junction-to-board characterization parameter	46	°C/W	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W	

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



5.7 Electrical Characteristics

at $T_A = 25^{\circ}C$, $V_S = \pm 15V$, $R_L = 2k\Omega$ connected to midsupply, and $V_{CM} = V_{OUT} = \text{midsupply}$ (unless otherwise noted)

	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
OFFSET V	DLTAGE						
V _{os}	Input offset voltage	OPAx132U			±0.2	±0.5	mV
* US	input onset voitage	OPAx132UA			±0.5	±2	
dV _{OS} /dT	Input offset voltage drift	T _A = -40°C to +85°C			±2	±10	μV/°C
PSRR	Power-supply rejection ratio	±2.5V ≤ V _S ≤ ±18V	OPAx132U		±5	±15	μV/V
FOILIT	r ower-supply rejection ratio	12.3V 3 VS 3 1 10V	OPAx132UA		±5	±30	μν/ν
	Channel separation (dual and quad)	$R_L = 2k\Omega$			0.2		μV/V
INPUT BIAS	S CURRENT						
	Input bias current ⁽¹⁾				±5	±50	20
I _B	input bias current	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		See Typ	ical Characteris	stics	pA
I _{OS}	Input offset current ⁽¹⁾				±2	±50	pА
NOISE						'	
		f = 10Hz			23		
		f = 100Hz			10		\ //
e _n	Input voltage noise density	f = 1kHz			8		nV/√Hz
		f = 10kHz			8		
In	Input current noise density	f = 1kHz			3		fA/√Hz
INPUT VOL	TAGE					1	
V _{CM}	Common-mode voltage			(V-) + 2.5	±13	(V+) - 3.5	V
01405		40.57/ 47/	OPAx132U	96	100		
CMRR	Common-mode rejection ratio	$-12.5V \le V_{CM} \le 11.5V$	OPAx132UA	86	94		dB
INPUT IMP	EDANCE						
	Differential			10 ¹³ 10			
	Common-mode	-12.5V ≤ V _{CM} ≤ 11.5V			10 ¹³ 7		Ω pF
OPEN-LOO	P GAIN						
		$R_L = 10k\Omega$,	OPAx132U	110	120		dB
		-14.5V ≤ V _O ≤ 13.8V	OPAx132UA	104	120		
		$R_{L} = 2k\Omega,$ $-13.8V \le V_{O} \le 13.5V$ $R_{L} = 600\Omega,$	OPAx132U	110	126		
A _{OL}	Open-loop voltage gain		OPAx132UA	104	120		
			OPAx132U	110	130		
		$-12.8V \le V_O \le 12.5V$	OPAx132UA	104	120		
FREQUENC	CY RESPONSE						
GBW	Gain bandwidth product				8		MHz
SR	Slew rate				±20		V/µs
			0.1%		0.7		
	Settling time	10V step, G = 1, C _L = 100pF	0.01%		1		μs
			$R_L = 2k\Omega$		0.0008%		
THD+N	Total harmonic distortion plus noise	$f = 1kHz, G = 1, V_O = 3.5V_{rms}$	R _L = 600Ω		0.0009%		
	Overload recovery time	G = ±1			600		ns
OUTPUT	· · · · · · · · · · · · · · · · · · ·	<u> </u>					
			Positive	(V+) - 1.2	(V+) - 0.9		
		$R_L = 10k\Omega$	Negative	, ,	(V-) + 0.3	(V-) + 0.5	
			Positive	(V+) - 1.5	(V+) – 1.1	. ,	V
Vo	Voltage output	$R_L = 2k\Omega$	Negative	(**,	(V-) + 1.2	(V-) + 0.9	
			Positive	(V+) - 2.5	(V+) - 2.0	(1 / 1 0.0	
		$R_L = 600\Omega$	Negative	(**, 2.3	(V-) + 2.2	(V-) + 1.5	
		Sourcing	9~~~		36	(*) * 1.5	mA
I _{sc}	Short-circuit current	Sinking			-30		mA
	Capacitive load drive (stable operation)	Officing		See Tim	ical Characteris	etics	IIIA
POWER SU				Зее тур	ioai OriardUlelli	,,,,,,,	
・ しいして ろし	// I E1						

⁽¹⁾ High-speed test at $T_J = 25$ °C.



5.8 Typical Characteristics

at $T_A = 25$ °C, $V_S = \pm 15$ V, $R_L = 2k\Omega$ connected to midsupply, and $V_{CM} = V_{OUT} =$ midsupply (unless otherwise noted)

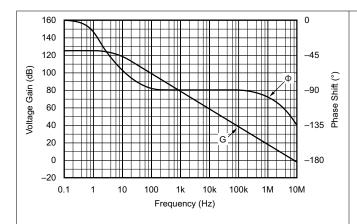
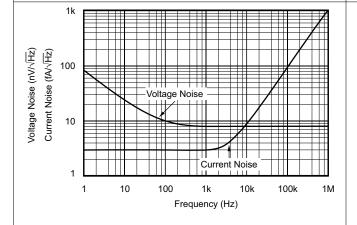


Figure 5-1. Open-Loop Gain and Phase vs Frequency

Figure 5-2. Power Supply and Common-Mode Rejection vs Frequency



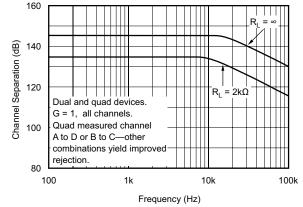
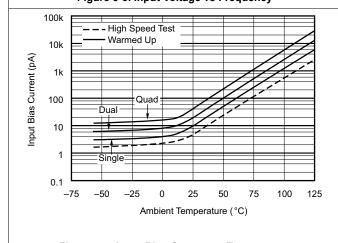


Figure 5-3. Input Voltage vs Frequency

Figure 5-4. Channel Separation vs Frequency



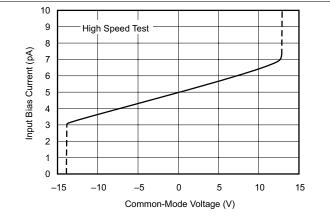


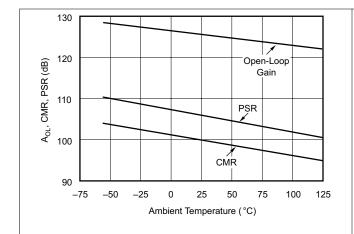
Figure 5-5. Input Bias Current vs Temperature

Figure 5-6. Input Bias Current vs Input Common-Mode Voltage



5.8 Typical Characteristics (continued)

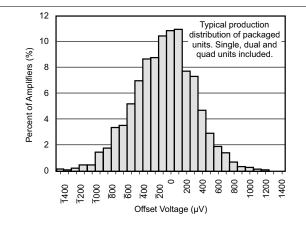
at $T_A = 25^{\circ}C$, $V_S = \pm 15V$, $R_L = 2k\Omega$ connected to midsupply, and $V_{CM} = V_{OUT} =$ midsupply (unless otherwise noted)



4.3 60 Quiescent Current Per Amp (mA) 4.2 50 Short-Circuit Current (mA) 4.1 4.0 3.9 20 3.8 10 -75 -50 -25 0 25 50 75 100 125 Ambient Temperature (°C)

Figure 5-7. A_{OL}, CMR, PSR vs Temperature

Figure 5-8. Quiescent Current and Short-Circuit Current vs
Temperature



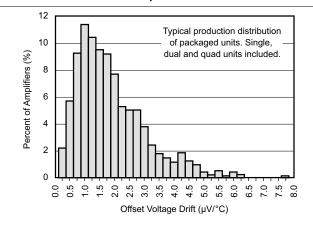


Figure 5-9. Offset Voltage Production Distribution

Figure 5-10. Offset Voltage Drift Production Distribution

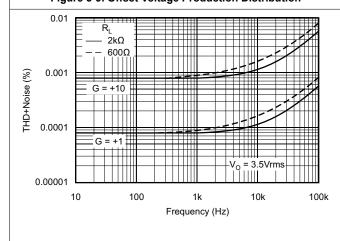


Figure 5-11. Total Harmonic Distortion + Noise vs Frequency

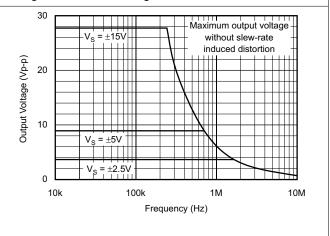
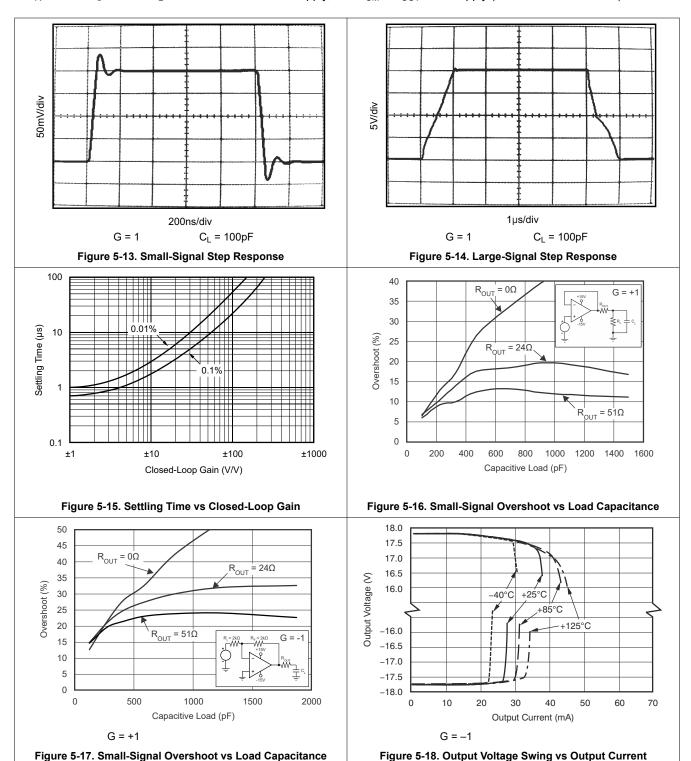


Figure 5-12. Maximum Output Voltage vs Frequency



5.8 Typical Characteristics (continued)

at $T_A = 25$ °C, $V_S = \pm 15$ V, $R_L = 2k\Omega$ connected to midsupply, and $V_{CM} = V_{OUT} =$ midsupply (unless otherwise noted)



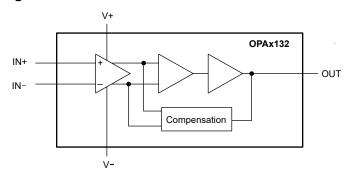


6 Detailed Description

6.1 Overview

The OPAx132 series of FET-input operational amplifiers provides high speed and excellent dc performance. The combination of high slew rate and wide bandwidth provide fast settling time. Single, dual, and quad versions have identical specifications for maximum design flexibility. High performance grades are available in the single and dual versions. All devices are an excellent choice for general-purpose, audio, data acquisition and communications applications; especially, where high source impedance is encountered.

6.2 Functional Block Diagram



6.3 Feature Description

The OPAx132 series of JFET operational amplifiers combine low noise and wide bandwidth with precision and low input bias current to make the these devices an excellent choice for applications with a high source impedance. The OPAx132 is unity-gain stable and features high slew rate (±20V/µs) and wide bandwidth (8MHz).

6.4 Device Functional Modes

The OPAx132 has a single functional mode and is operational when the power-supply voltage is greater than 5V (±2.5V). The maximum power supply voltage for the OPAx132 is 36V (±18V).

7 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

The OPAx132 series operational amplifiers are unity-gain stable and an excellent choice for a wide range of general-purpose applications. Bypass power-supply pins with 10nF ceramic capacitors or larger.

The OPAx132 series operational amplifiers are free from unexpected output phase reversal common with FET operational amplifiers. Many FET-input operational amplifiers exhibit phase-reversal of the output when the input common-mode voltage range is exceeded. This phase reversal can occur in voltage-follower circuits, causing serious problems in control-loop applications. The OPAx132 series of operational amplifiers are free from this undesirable behavior. All circuitry is completely independent in dual and quad versions, maintaining normal behavior when one amplifier in a package is overdriven or short-circuited.

7.1.1 Operating Voltage

The OPAx132 series of operation amplifiers operate with power supplies from ±2.5V to ±18V with excellent performance. Although specifications are production tested with ±15V supplies, most behavior remains unchanged throughout the full operating voltage range. Parameters which vary significantly with operating voltage are shown in Section 5.8.

7.1.2 Offset Voltage Trim

The offset voltage of the OPAx132 amplifiers is laser trimmed and usually requires no user adjustment. The OPAx132 provide less than $\pm 500 \mu V$ of input offset voltage and less than $10 \mu V$ /°C of input offset voltage drift over the operating temperature range

7.1.3 Input Bias Current

The FET-inputs of the OPAx132 series provide very low input bias current and cause negligible errors in most applications. For applications where low input bias current is crucial, minimize junction temperature rise. The input bias current of FET-input operational amplifiers increases with temperature; see also Figure 5-5.

The OPAx132 series can be operated at reduced power supply voltage to minimize power dissipation and temperature rise. Using ±3V supplies reduces power dissipation to one-fifth used at ±15V.

The dual and quad versions have higher total power dissipation than the single version, leading to higher junction temperature. Thus, a warmed-up quad has higher input bias current than a warmed-up single. Furthermore, an SOIC generally has higher junction temperature than a DIP at the same ambient temperature because of a larger θ_{JA} .

Printed-circuit-board (PCB) layout also helps minimize junction temperature rise. Minimize temperature rise by soldering the devices to the PCB rather than using a socket. Wide copper traces also help dissipate the heat by acting as an additional heat sink.

Input stage cascode circuitry keeps the input bias current virtually unchanged throughout the full input common-mode range of the OPAx132 series. See also Figure 5-6.



7.2 Typical Application

The OPAx132 family offers outstanding dc precision and ac performance. These devices operate up to 36V supply rails and offer ultra-low input bias current and input bias current noise, as well as 8MHz bandwidth and high capacitive load drive. These features make the OPAx132 a robust, high-performance operational amplifier for high-voltage industrial applications with high source impedance.

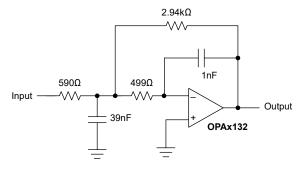


Figure 7-1. OPA132 2nd Order 30kHz, Low Pass Filter Schematic

7.2.1 Design Requirements

Use the following parameters for this application:

- Gain = 5V/V
- Low-pass cutoff frequency = 30kHz
- –40db/dec filter response
- Maintain less than 3dB gain peaking in the gain versus frequency response

7.2.2 Detailed Design Procedure

WEBENCH® Circuit Designer creates customized power supply and active filter circuits based on your system requirements. The environment gives you end-to-end selection, design, and simulation capabilities that save you time during all phases of the analog design process.

Use our tools to help with your designs:

- · Filter design tool
- Powerstage designer
- WEBENCH® Power designer
- PCB thermal calculator

7.2.3 Application Curve

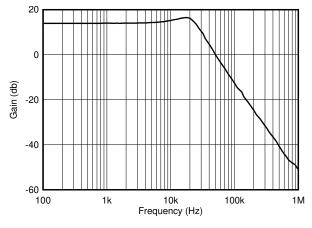


Figure 7-2. OPA132 2nd-Order 30kHz, Low-Pass Filter Response

7.3 Power Supply Recommendations

The OPAx132 is specified for operation from 5V to 36V (±2.5V to ±18V); many specifications apply from –40°C to +85°C. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in Section 5.8.

CAUTION

Supply voltages larger than 36V can permanently damage the device; see Section 5.1.

Place 10nF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see Section 7.4.1.

7.4 Layout

7.4.1 Layout Guidelines

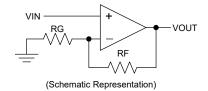
For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the operational
 amplifier individually. Use bypass capacitors to reduce the coupled noise by providing low-impedance power
 sources local to the analog circuitry.
 - Connect low-ESR, 10nF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective
 methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
 A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
 and analog grounds paying attention to the flow of the ground current. For more detailed information, see
 also Circuit Board Layout Techniques.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keep RF and RG close to the inverting input minimizes parasitic capacitance; see also *Section 7.4.2*.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Clean the PCB following board assembly for best performance.
- Any precision integrated circuit can experience performance shifts due to moisture ingress into the plastic package. Following any aqueous PCB cleaning process, bake the PCB assembly to remove moisture introduced into the device packaging during the cleaning process. A low temperature, post cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

Submit Document Feedback



7.4.2 Layout Example



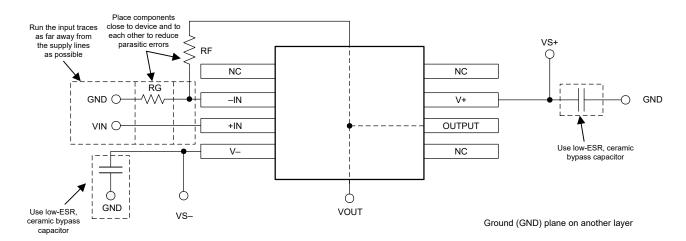


Figure 7-3. OPA132 Layout Example for the Noninverting Configuration



8 Device and Documentation Support

8.1 Device Support

8.1.1 Development Support

8.1.1.1 Analog Filter Designer

Available as a web-based tool from the Design and simulation tool web page, the Analog Filter Designer allows the user to design, optimize, and simulate complete multistage active filter solutions within minutes.

8.1.1.2 TINA-TI™ Simulation Software (Free Download)

TINA-TI™ simulation software is a simple, powerful, and easy-to-use circuit simulation program based on a SPICE engine. TINA-TI simulation software is a free, fully-functional version of the TINA™ software, preloaded with a library of macromodels, in addition to a range of both passive and active models. TINA-TI simulation software provides all the conventional dc, transient, and frequency domain analysis of SPICE, as well as additional design capabilities.

Available as a free download from the Design tools and simulation web page, TINA-TI simulation software offers extensive post-processing capability that allows users to format results in a variety of ways. Virtual instruments offer the ability to select input waveforms and probe circuit nodes, voltages, and waveforms, creating a dynamic quick-start tool.

Note

These files require that either the TINA software or TINA-TI software be installed. Download the free TINA-TI simulation software from the TINA-TI™ software folder.

8.1.1.3 TI Reference Designs

TI reference designs are analog solutions created by TI's precision analog applications experts. TI reference designs offer the theory of operation, component selection, simulation, complete PCB schematic and layout, bill of materials, and measured performance of many useful circuits. TI reference designs are available online at https://www.ti.com/reference-designs.

8.2 Documentation Support

8.2.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, EMI Rejection Ratio of Operational Amplifiers
- Texas Instruments, Circuit Board Layout Techniques

8.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.4 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

8.5 Trademarks

TINA-TI™ and TI E2E™ are trademarks of Texas Instruments.

TINA™ is a trademark of DesignSoft, Inc.

All trademarks are the property of their respective owners.



8.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.7 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (September 2015) to Revision C (August 2024) Page Added information about newer, next-generation OPA2156...... Changed input voltage from (V-) - 0.7 and (V+) + 0.7 to (V-) - 0.5 and (V+) + 0.5 in Absolute Maximum Ratings5 Added Thermal Information6 Changed common-mode voltage MAX value from (V+) – 2.5V to (V+) – 3.5V......7 Changed common-mode rejection ratio and common-mode input impedance test conditions from −12.5V ≤ $V_{CM} \le 12.5V \text{ to } -12.5V \le V_{CM} \le 11.5V.....$ Changed differential input impedance from $10^{10}\Omega$ || 2pF to $10^{10}\Omega$ || 10pF.......7 Changed common-mode input impedance from $10^{10}\Omega$ || 6pF to $10^{10}\Omega$ || 7pF....... Deleted redundant power supply and temperature range sections already covered in Recommended Changed Figure 16, Small-Signal Overshoot vs Load Capacitance into two plots, Figure 5-16 for G = +1 and Updated Figure 7-3, OPA132 Layout Example for the Noninverting Configuration15



Changes from Revision A (June 2004) to Revision B (September 2015)

Page

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Submit Document Feedback

Copyright © 2024 Texas Instruments Incorporated

www.ti.com

21-Sep-2024

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
OPA132U	ACTIVE	SOIC	D	8	75	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR		OPA 132U	Samples
OPA132U/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR		OPA 132U	Samples
OPA132UA	ACTIVE	SOIC	D	8	75	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR	-40 to 125	OPA 132U A	Samples
OPA132UA/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR	-40 to 125	OPA 132U A	Samples
OPA2132P	ACTIVE	PDIP	Р	8	50	RoHS & Green	Call TI	N / A for Pkg Type		OPA2132P	Samples
OPA2132PA	ACTIVE	PDIP	Р	8	50	RoHS & Green	Call TI	N / A for Pkg Type		OPA2132P A	Samples
OPA2132PAG4	ACTIVE	PDIP	Р	8	50	RoHS & Green	Call TI	N / A for Pkg Type		OPA2132P A	Samples
OPA2132U	ACTIVE	SOIC	D	8	75	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR	-40 to 125	(O2132U, OPA) 2132U	Samples
OPA2132U/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	Call TI NIPDAU	Level-3-260C-168 HR	-40 to 125	(O2132U, OPA) 2132U	Samples
OPA2132UA	ACTIVE	SOIC	D	8	75	RoHS & Green	Call TI	Level-3-260C-168 HR	-40 to 125	OPA 2132U A	Samples
OPA2132UA/2K5	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	OPA 2132U A	Samples
OPA4132UA	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU NIPDAU-DCC	Level-3-260C-168 HR	-40 to 85	OPA4132UA	Samples
OPA4132UA/2K5	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU NIPDAU-DCC	Level-3-260C-168 HR	-40 to 85	OPA4132UA	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.



PACKAGE OPTION ADDENDUM

www.ti.com 21-Sep-2024

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: Til defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 12-Jun-2024

TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

	-
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

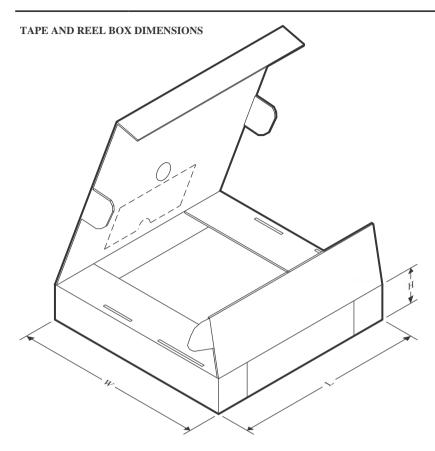


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA132U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA132UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2132U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2132U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2132UA/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA4132UA/2K5	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1



www.ti.com 12-Jun-2024



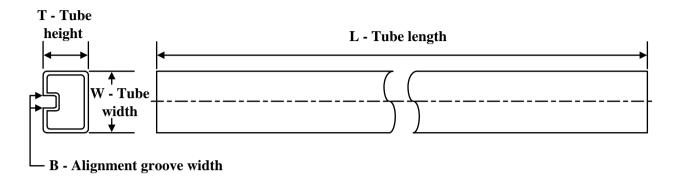
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA132U/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA132UA/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA2132U/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA2132U/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA2132UA/2K5	SOIC	D	8	2500	356.0	356.0	35.0
OPA4132UA/2K5	SOIC	D	14	2500	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION

www.ti.com 12-Jun-2024

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
OPA132U	D	SOIC	8	75	506.6	8	3940	4.32
OPA132U	D	SOIC	8	75	506.6	8	3940	4.32
OPA132UA	D	SOIC	8	75	506.6	8	3940	4.32
OPA132UA	D	SOIC	8	75	506.6	8	3940	4.32
OPA2132P	Р	PDIP	8	50	506	13.97	11230	4.32
OPA2132PA	Р	PDIP	8	50	506	13.97	11230	4.32
OPA2132PAG4	Р	PDIP	8	50	506	13.97	11230	4.32
OPA2132U	D	SOIC	8	75	506.6	8	3940	4.32
OPA2132U	D	SOIC	8	75	506.6	8	3940	4.32
OPA2132UA	D	SOIC	8	75	506.6	8	3940	4.32
OPA2132UA	D	SOIC	8	75	506.6	8	3940	4.32
OPA2132UE4	D	SOIC	8	75	506.6	8	3940	4.32
OPA2132UE4	D	SOIC	8	75	506.6	8	3940	4.32
OPA4132UA	D	SOIC	14	50	506.6	8	3940	4.32

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





SMALL OUTLINE INTEGRATED CIRCUIT



- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2024, Texas Instruments Incorporated